

# Erratum to: Structural and Thermoelectric Properties of Nanocrystalline Bismuth Telluride Thin Films Under Compressive and Tensile Strain

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Following are corrections to the original article:

1. Figure 5 is corrected as shown in this erratum.
2. Due to this change, the relationship between the direction of strain and the in-plane thermoelectric properties becomes opposite trends, presenting in section of Abstract, Thermoelectric Properties of Strained Bismuth Telluride Thin Films, and Conclusion.
3. The section of Thermoelectric Properties of Strained Bismuth Telluride Thin Films, first paragraph: “One possible explanation of the increase in electrical conductivity....” should be deleted. In addition, reference 28 should be also deleted.
4. The section of Thermoelectric Properties of Strained Bismuth Telluride Thin Films, third paragraph: “Compared with previously....indicative of trends opposite to those observed....” should be “Compared with previously....indicative of similar trends to those observed....”
5. The section of Thermoelectric Properties of Strained Bismuth Telluride Thin Films, of third paragraph from “The reason our results differ from....” to the end of the paragraph should be deleted.

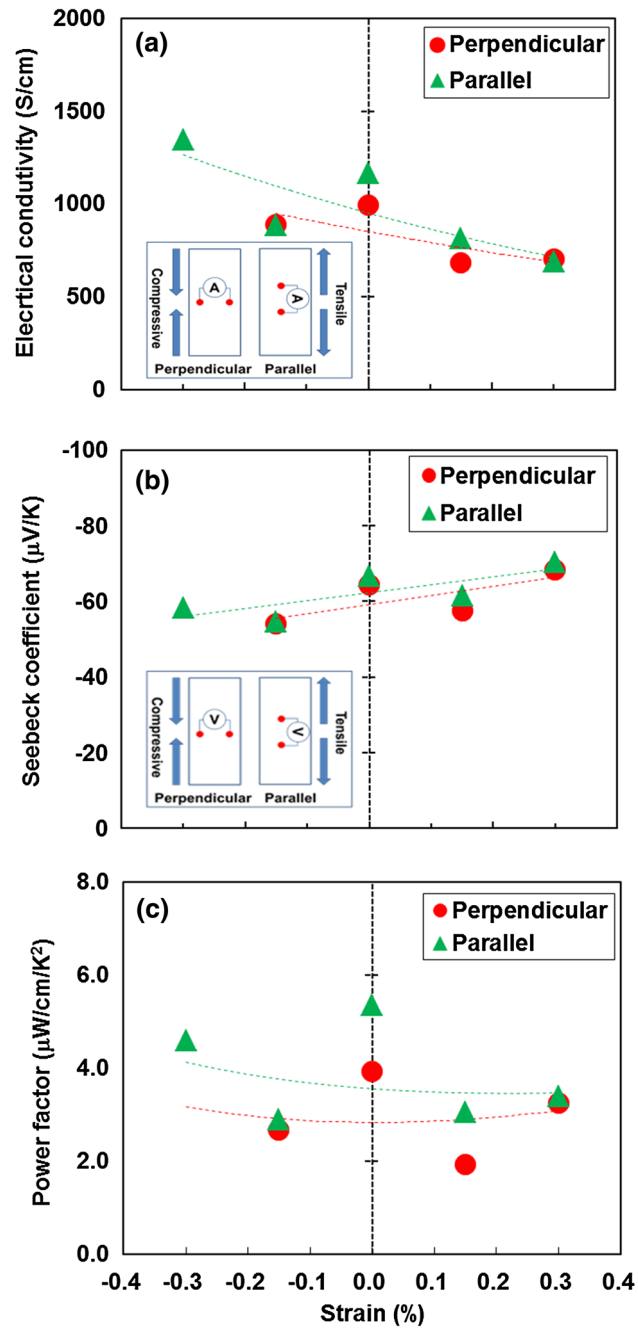


Fig. 5. (a) Electrical conductivity, (b) Seebeck coefficient, and (c) power factor of bismuth telluride thin films as a function of applied strain.